

QUAD TVS/ZENER FOR ESD AND LATCH-UP PROTECTION

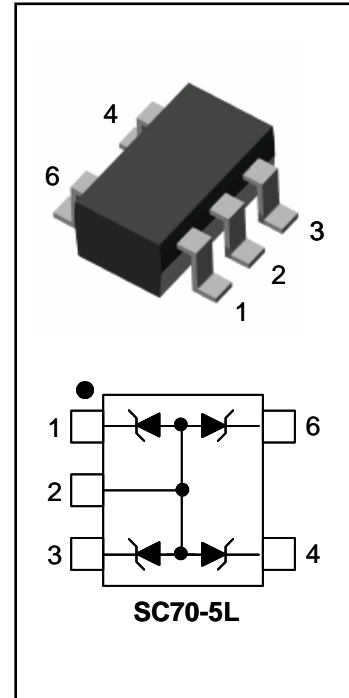
This Quad TVS/Zener Array has been designed to Protect Sensitive Equipment against ESD and to prevent Latch-Up events in CMOS circuitry operating at 5Vdc and below. This TVS array offers an integrated solution to protect up to 4 data lines where the board space is a premium.

SPECIFICATION FEATURES

- 150W Power Dissipation (8/20 μ s Waveform)
- Very Low Leakage Current, Maximum of 5 μ A @ 5Vdc
- Very low Clamping voltage (Max of 10V @ 14A 8/20 μ s)
- IEC61000-4-2 ESD 15kV air, 8kV Contact Compliance
- Industry standard SOT353 (Also known as SC70-5L)

APPLICATIONS

- Personal Digital Assistant (PDA)
- SIM Card Port Protection (Mobile Phone)
- Portable Instrumentation
- Mobile Phones and Accessories
- Computer Data Ports



MAXIMUM RATINGS

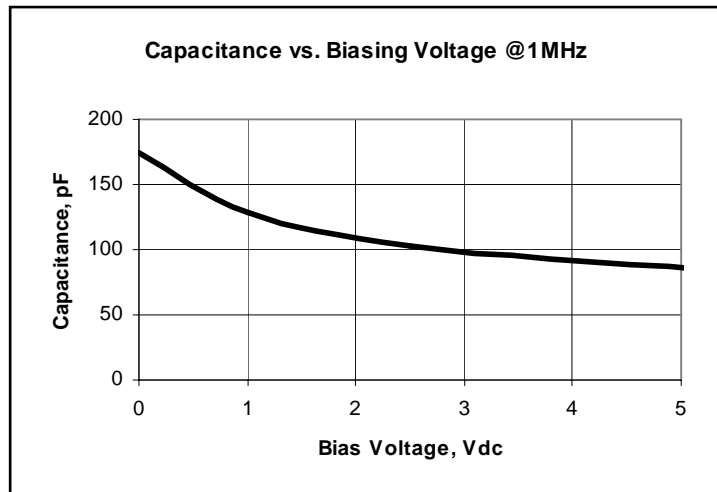
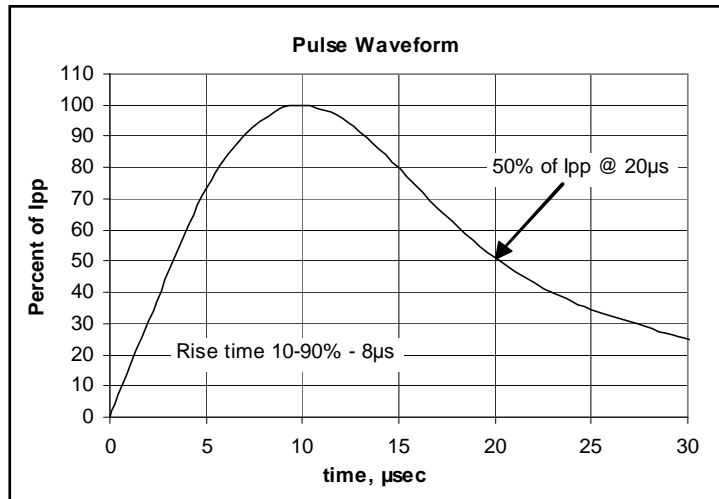
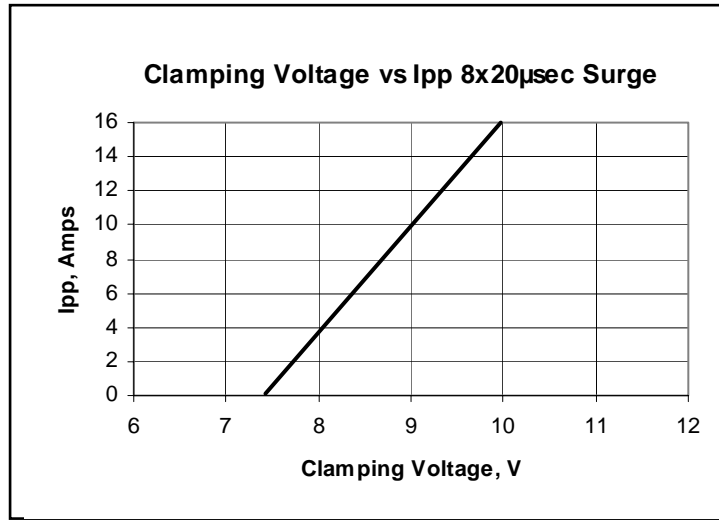
Rating	Symbol	Value	Units
Peak Pulse Power (8/20 μ s Waveform)	P_{pp}	150	W
Peak Pulse Current (8/20 μ s Waveform)	I_{pp}	14	A
ESD Voltage (HBM)	V_{ESD}	>25	kV
Operating Temperature Range	T_J	-55 to +150	$^{\circ}$ C
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS $T_j = 25^{\circ}$ C

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{WRM}				5	v
Reverse Breakdown Voltage	V_{BR}	$I_{BR} = 1$ mA	6.2		7.2	V
Reverse Leakage Current	I_R	$V_R = 5$ V			5	μ A
Clamping Voltage (8/20 μ s)	V_C	$I_{pp} = 5$ Amps			8.6	V
Clamping Voltage (8/20 μ s)	V_C	$I_{pp} = 10$ Amps			9.1	V
Off State Junction Capacitance	C_j	0 Vdc Bias f = 1MHz Between I/O pins and pin 7			180	pF
Off State Junction Capacitance	C_j	5 Vdc Bias f = 1MHz Between I/O pins and pin 7			90	pF

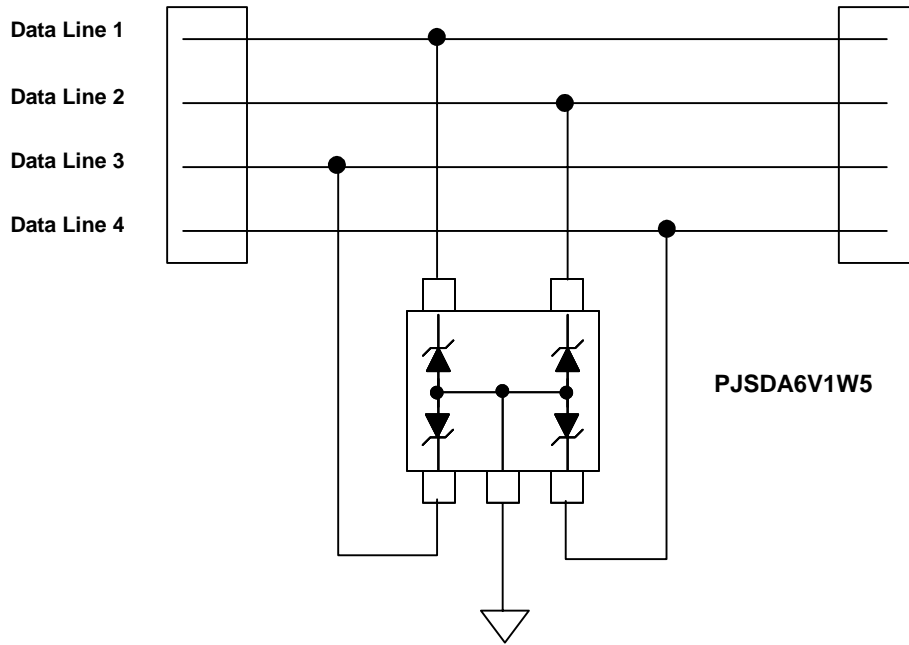
TYPICAL CHARACTERISTICS

PRELIMINARY



TYPICAL APPLICATION EXAMPLE AND PACKAGE LAYOUT DIMENSIONS

PRELIMINARY



**SIM Card Port
or Phone Port**

